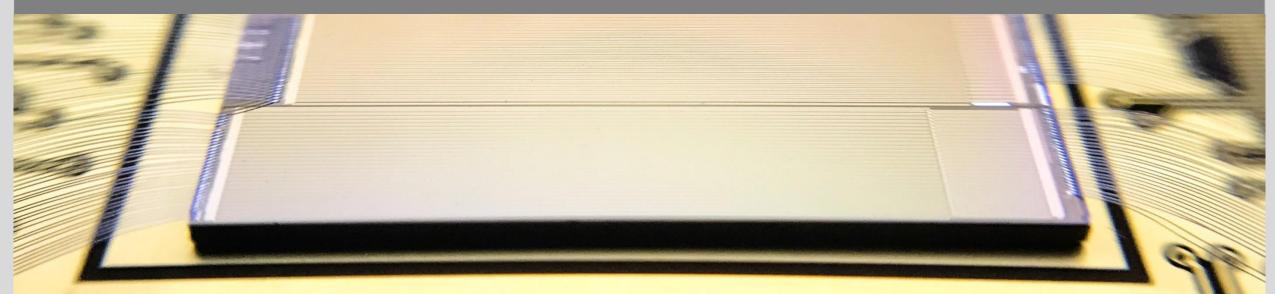


The MuPix 10 – the current state of design

Alena Weber for the Mu3e Collaboration

ASIC and Detector Laboratory, Karlsruhe Institute of Technology and University Heidelberg

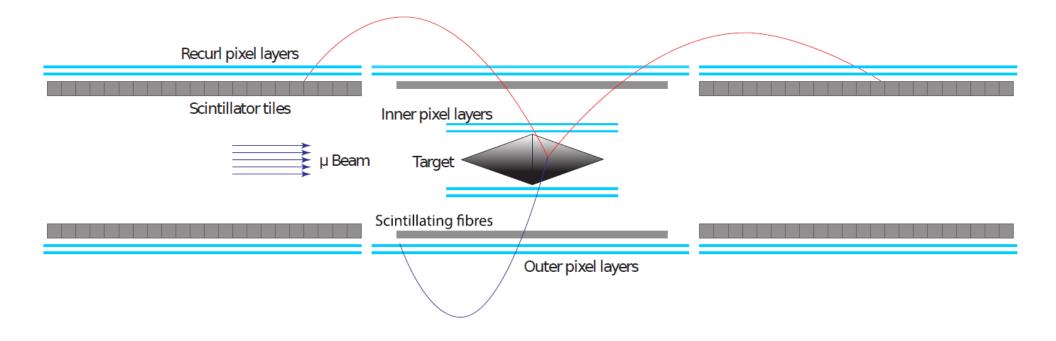


The Mu3e Experiment

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- Searching for $\mu^+ \rightarrow e^+ e^- e^+$
- Main requirements of the detector:
 - Precise tracking
 - Minimal material budget

- High Voltage Monolithic Active Pixel Sensors (HV-MAPS) fulfil requirements
- Chosen for tracking layers
- \rightarrow On track to the final chip



26.03.2019

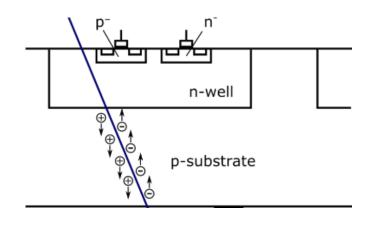
2

HVCMOS

= High Voltage Complementary Metal Oxide Semiconductor

Features

- Fast and efficient charge collection by drift
- Sensor and electronics on the same die
 → monolithic
- Low cost
- Thinned to 50 μm

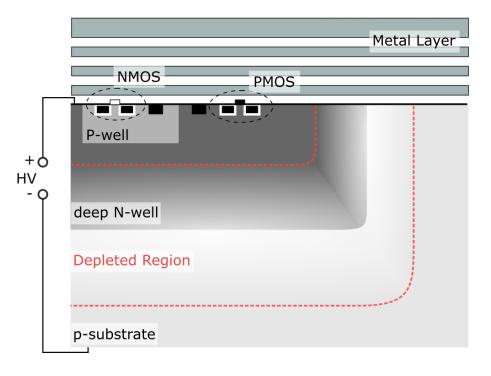


Properties

■ High depletion voltage ≈ -150 V

Highℝ ∖ ⁺++

- 30 µm depletion depth
- Standard process



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Karleruhar Instit

Overview of the latest MuPix and ATLASPix sensors





Main Challenges



Surrounding

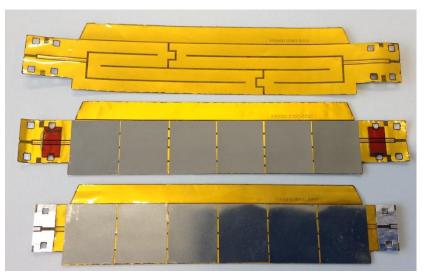
- Full size: active sensor size ≈ 2 x 2 cm²
- Move to new technology
 From AMS to TSI
- One single supply voltage

Aim

Provide a chip for building functional Mu3e modules

Design Challenges

- Fully functional
- Operate multiple chips on flexprint
- Limited routing possibilities on flexprint



Parts of the existing mockup

Design transfer to another technology

AMS ah18

- Used for several prototypes > 10
- 6 metal layers

Chances

- One metal layer more: will be used for optimized routing
- Similar technology

TSI 180 nm HVCMOS

- First use in our group in 2018
- Submitted three chips
- Verification by comparison of MuPix7 in AMS and in TSI

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7 metal layers

Challenges

- Layout has to be redone for a few circuits
- Design rules different from metal 5 to the top
- Process similar but not the same

6

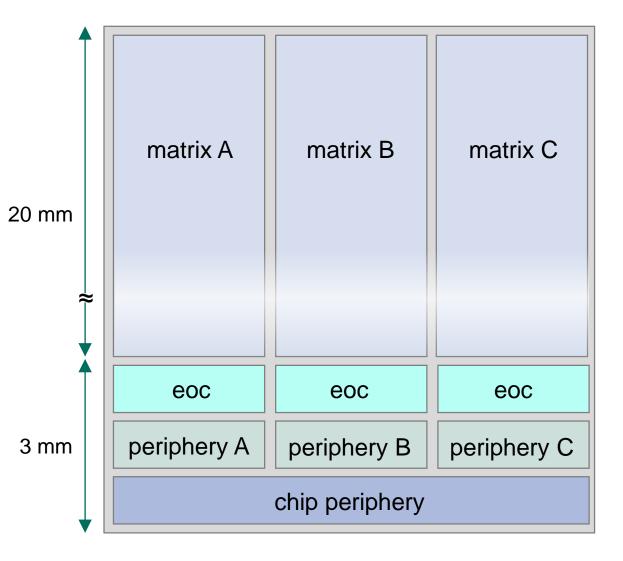
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Chip overview



Main parts

- Pixel matrix divided in three submatrices
- Pixel periphery with end of column (eoc)
- Submatrix periphery
- Chip periphery



7

Matrix Design – three submatrices



Common features

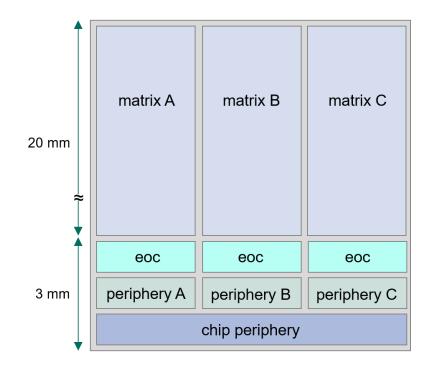
- Pixel size 80 x 80 μm²
- 250 pixels per column, in total 250 columns
- Same state machine but one for every matrix
- Chip periphery

Challenges

Operate all matrices at the same time with corresponding configuration and shared chip periphery

Separated parts and differences

- Configuration bits can be set individually
- Pixel amplifiers
- Signal transmission



Pixel Cell - Diode



Properties

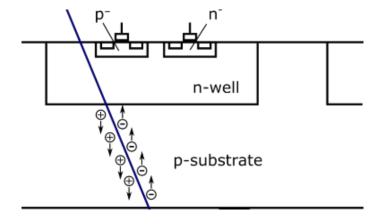
- Pixel size 80 x 80 μm²
- Diode formed by the deep n-well and p-substrate
- New geometry of n-well

Optimization

- Geometry of charge collection diode will be optimized with TCAD simulations
 - \rightarrow studies ongoing
- Goal: homogeneous electrical field distribution

Implementation and Verification

- One optimized geometry chosen for all matrices
- In first columns of matrix A different pixel geometries will be implemented to allow studies and verification



9

Pixel Cell - Amplifier



Properties

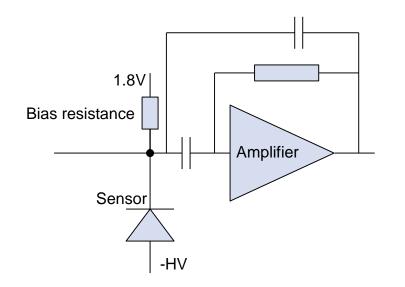
- Amplifier in pixel
- Every pixel maskable

CMOS Amplifier

- Implemented in ATLASPix 3
- Uses vdda = 1,8 V
 no additional voltage needed
- Matrix C

PMOS Amplifier

- Implemented in MuPix 8
- Vssa needed = 0,9 V
- Used successfully in many chips
- Matrix A and B



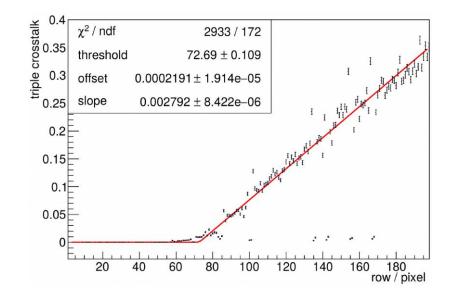
Signal Transmission

Source follower

Implemented in MuPix 8 matrix A

Current driver

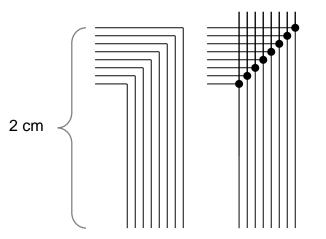
- Implemented in MuPix 8 matrices B and C
- Small design modifications needed



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Routing

- For routing in total 3 metal layers
- Routing scheme similar to ATLASPix 3
 - same line length
 - all lines with same shape
 - requires more time for routing
 - suppression of row-dependent change of pulse shape
 - more homogeneous time resolution



Readout Cell

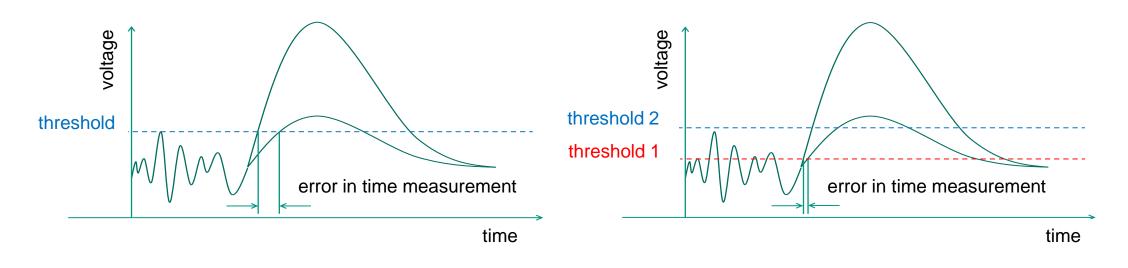


2 Threshold Method

- 2 Comparators per pixel like MuPix 8
- 3 bits per readout cell for threshold tuning
- Lower threshold voltage provides timestamp with less timewalk
- Higher threshold confirms signal

Data Rate

- 11 bits for timestamps
 1 bit more then MuPix 8
- 5 bits for TOT one bit less then MuPix 8
- \rightarrow same data format like MuPix 8
- sampling frequency 250 MHz



Chip Readout and Pads

Readout

- 3 LVDS links (one for every matrix)
- 1 LVDS link with multiplexed signals
- Max. LVDS data rate 1.6 Gbit/s

Monitor internal signals

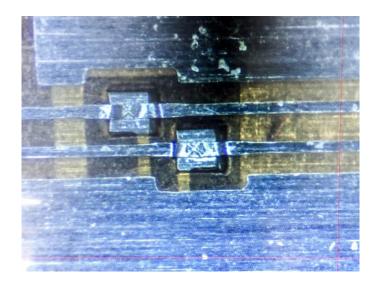
- Temperature
- Amplifier output
- Hitbus
- Bandgap voltage
- Power regulated voltages

Pads

 Minimized number of inputs and outputs to run the chip

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- All pads at the bottom
- Enough space for test to monitor internal signals
- Suitable for TAB-bonding

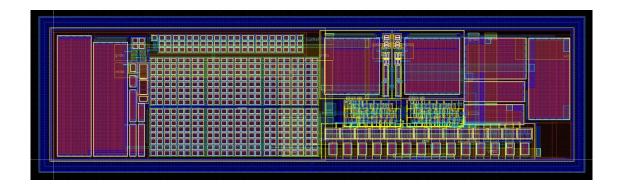


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Power Regulator

Properties

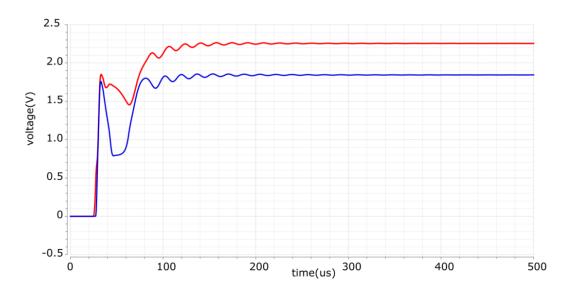
- In Mu3e: one supply voltage: 2.0 2.2 V
- Generates stable 1.8 V and 0.9 V
- Controlled by slow control
- Power separated:
 - Analogue and digital part separated
 - Capacitively coupled
 - Allow different voltage levels for optional serial powering with different schemes



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Status

- Power regulator designed for ATLASPix and MuPix
- Actual design submitted with ATLASPix 3



Simulation of 4 chips with power regulator connected in parallel

Summary



- Full size
- Suitable for module building
- A lot of features in one chip old ones, improved ones, new ones
- Different options in one chip including the final MuPix design
- Last prototype
- Final chip based on MuPix 10



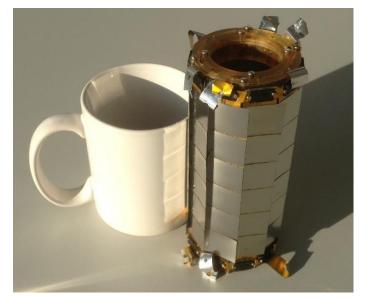


Photo of the existing mockup



BACKUP

Important features from other chips for MuPix 10



- 2 threshold mode MuPix 8
- 3 submatrices MuPix 8
- Pixels with PMOS amplifier MuPix 8
- Slow control MuPix 9
- Analog and digital power supply separated and capacitive coupled MuPix 9
- Power Regulator MuPix 9 and ATLASPix 3
- Pixels with CMOS amplifier ATLASPix 3

Power Regulator



- Only one supply voltage: 2.0 2.2 V
- Similar Power Regulator developed and implanted on ATLASPix 3, submitted in March
- Based on the results of the measurements of this power regulator the circuit will be optimised for MuPix 10
- Power Regulators controlled by slow control
- Power Regulators can be bypassed
- Power Up Reset with max 1 ms length
 - chip in standby
 - chip can be configured \rightarrow slow control is the only powered part
 - power regulators disabled
 - single chips tests without cooling possible
- Analogue and digital part separated regarding to power and capacitively coupled

 \rightarrow allow different voltage levels for optional serial powering with different schemes \rightarrow implemented in MuPix 9 \checkmark